

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A semiconductor device comprising:

a semiconductor substrate;

a conductive plug electrically connected to the semiconductor substrate and including

Si;

a flat electrically conductive silicon carbide film provided on the conductive plug;

a flat metal compound film provided on the flat electrically conductive silicon carbide film and containing a metal carbide; and

[[an]] a flat electrode provided on the flat metal compound film.

Claim 2 (Withdrawn): A semiconductor device comprising:

a semiconductor substrate;

a conductive plug electrically connected to the semiconductor substrate;

a silicon carbide film provided on the conductive plug;

a metal compound film provided on the silicon carbide film and containing a metal carbide;

a capacitor lower electrode provided on the metal compound film;

a capacitor upper electrode provided above the capacitor lower electrode; and

a capacitor dielectric film provided between the capacitor lower electrode and the capacitor upper electrode and containing a ferroelectric material or a highly dielectric material as a major component.

Claim 3 (Original): The semiconductor device according to claim 1, wherein the conductive plug is electrically connected to an active region of a transistor provided on the surface of the semiconductor substrate.

Claim 4 (Withdrawn): The semiconductor device according to claim 2, wherein the conductive plug is electrically connected to an active region of a transistor provided on the surface of the semiconductor substrate.

Claim 5 (Original): The semiconductor device according to claim 1, wherein the metal carbide contains a carbide of titanium, zirconium, hafnium, vanadium, niobium, or tantalum.

Claim 6 (Withdrawn): The semiconductor device according to claim 2, wherein the metal carbide contains a carbide of titanium, zirconium, hafnium, vanadium, niobium, or tantalum.

Claim 7 (Original): The semiconductor device according to claim 3, wherein the metal carbide contains a carbide of titanium, zirconium, hafnium, vanadium, niobium, or tantalum.

Claim 8 (Withdrawn): The semiconductor device according to claim 4, wherein the metal carbide contains a carbide of titanium, zirconium, hafnium, vanadium, niobium, or tantalum.

Claim 9 (Currently Amended): The semiconductor device according to claim 1, wherein the flat metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

Claim 10 (Withdrawn): The semiconductor device according to claim 2, wherein the metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

Claim 11 (Currently Amended): The semiconductor device according to claim 3, wherein the flat metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

Claim 12 (Withdrawn): The semiconductor device according to claim 4, wherein the metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

Claim 13 (Currently Amended): The semiconductor device according to claim 5, wherein the flat metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

Claim 14 (Withdrawn): The semiconductor device according to claim 6, wherein the metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

Claim 15 (Currently Amended): The semiconductor device according to claim 7, wherein the metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

Claim 16 (Withdrawn): The semiconductor device according to claim 8, wherein the metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

Claim 17 (Withdrawn): A method of manufacturing a semiconductor device comprising:

- preparing a semiconductor substrate;
- forming a conductive plug electrically connected to the semiconductor substrate;
- forming a silicon carbide film covering an upper surface of the conductive plug;
- forming a first metal film on the silicon carbide film;
- forming a second metal film on the first metal film;
- forming a dielectric film containing a ferroelectric material or a highly dielectric material which is a major component on the second metal film; and
- forming a metal compound film on the silicon carbide film by heat treatment in an oxidizing atmosphere, the metal compound film comprising a metal carbide of a metal contained in the first metal film and carbon.

Claim 18 (Withdrawn): The method according to claim 17, wherein the first metal film is a titanium film, zirconium film, hafnium film, vanadium film, niobium film, or tantalum film.

Claim 19 (Withdrawn): The method according to claim 17, further comprising:
forming a third metal film on the metal compound film; processing the third metal film, the metal compound film, the dielectric film, the second metal film, and the silicon carbide film by etching; and carrying out a heat treatment in an oxidizing atmosphere.

Claim 20 (Withdrawn): The method according to claim 18, further comprising:
forming a third metal film on the metal compound film; processing the third metal film, the metal compound film, the dielectric film, the second metal film, and the silicon carbide film by etching; and carrying out a heat treatment in an oxidizing atmosphere.

Claim 21 (Withdrawn): The method according to claim 17, wherein the dielectric film is a capacitor dielectric film, and the second and third metal films are capacitor lower and upper electrodes.

Claim 22 (Withdrawn): The method according to claim 18, wherein the dielectric film is a capacitor dielectric film, and the second and third metal films are capacitor lower and upper electrodes.

Claim 23 (Withdrawn): The method according to claim 19, wherein the dielectric film is a capacitor dielectric film, and the second and third metal films are capacitor lower and upper electrodes.

Claim 24 (Withdrawn): The method according to claim 20, wherein the dielectric film is a capacitor dielectric film, and the second and third metal films are capacitor lower and upper electrodes.